

TOSHIBA INTEGENT POWER MODULE SILICON N CHANNEL IGBT

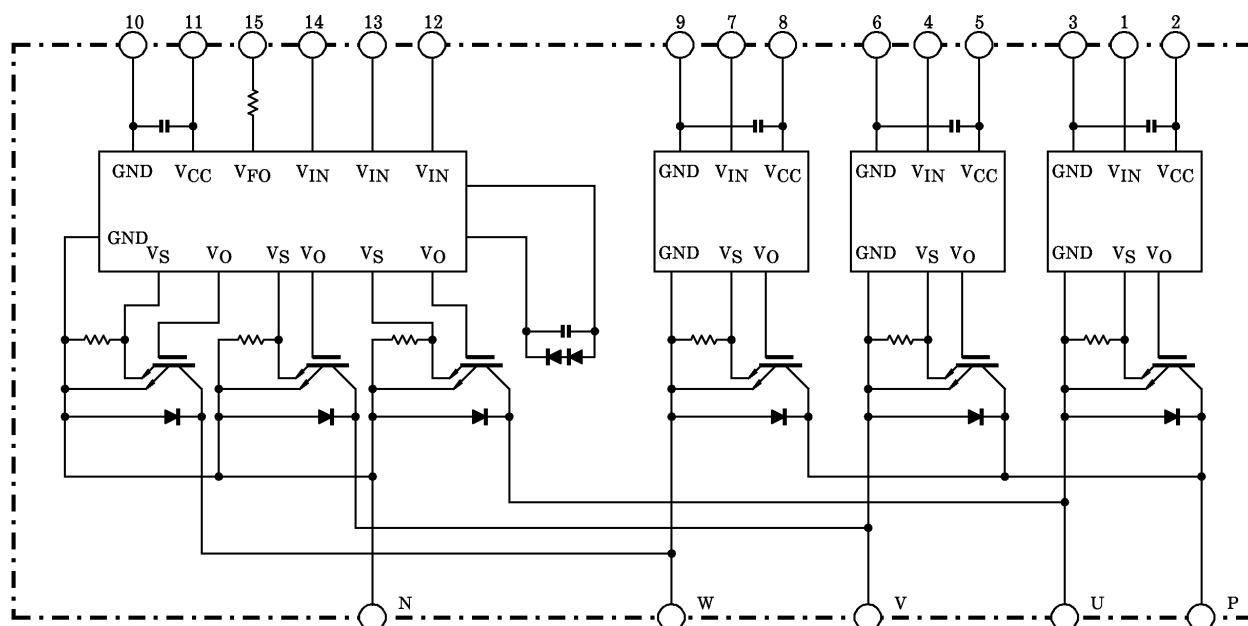
MIG30J103HB

HIGH POWER SWITCHING APPLICATIONS

MOTOR CONTROL APPLICATIONS

- Intelligent Power Module that include IGBT drive circuits, overcurrent, undervoltage lockout, and overtemperature protection.
- The Electrodes are Isolated from Case.
- High speed type IGBT : $V_{CE(sat)}=2.7V$ (MAX.)
 $t_{off}=2.0\mu s$ (MAX.)
 $t_{rr}=0.25\mu s$ (MAX.)
- Outline : TOSHIBA 2-99E1A
- Weight : 80g

EQUIVALENT CIRCUIT



- | | | |
|---------------|---------------|---------------|
| 1. V_{INU} | 2. V_{DU} | 3. GND_U |
| 4. V_{INV} | 5. V_{DV} | 6. GND_V |
| 7. V_{INW} | 8. V_{DW} | 9. GND_W |
| 10. GND_L | 11. V_{DL} | 12. V_{INX} |
| 13. V_{INY} | 14. V_{INZ} | 15. V_{FO} |

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MAXIMUM RATINGS ($T_j = 25^\circ\text{C}$)

	SYMBOL	ITEM	CONDITION	RATING	UNIT
Inverter Part	V_{CC}	Supply Voltage	P-N	400	V
	V_{CES}	Collector-Emitter Voltage	—	600	V
	$\pm I_C$	Collector Current (DC)	$T_c = 25^\circ\text{C}$	30	A
	P_C	Collector Power Dissipation	$T_c = 25^\circ\text{C}$	100	W
	T_j	Junction Temperature	—	150	$^\circ\text{C}$
Control Part	V_D	Supply Voltage	—	20	V
	V_{IN}	Input Voltage	$V_{IN} = V_D$	20	V
	V_{FO}	Foul Output Voltage	$V_{FO} = V_D$	20	V
	I_{FO}	Foul Output Current	—	7	mA
All System	T_c	Operating Temperature	—	$-20 \sim +100$	$^\circ\text{C}$
	T_{stg}	Storage Temperature Range	—	$-40 \sim +125$	$^\circ\text{C}$
	V_{ISO}	Isolation Voltage	AC, 1 min	2500	V_{rms}
	—	Screw Torque	M5	2	N·m

ELECTRICAL CHARACTERISTICS ($T_j = 25^\circ\text{C}$)

Inverter Part

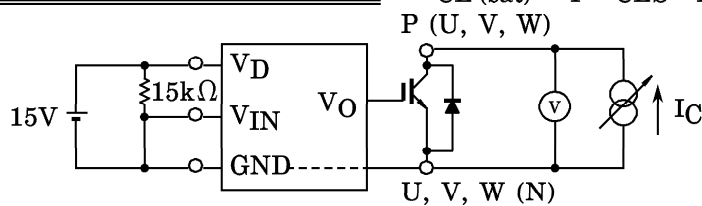
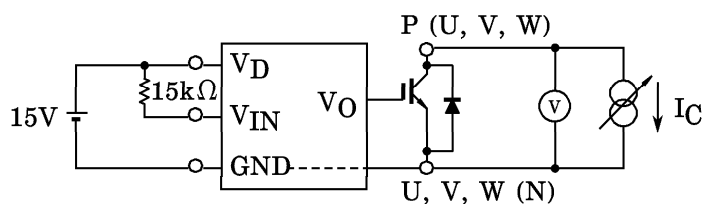
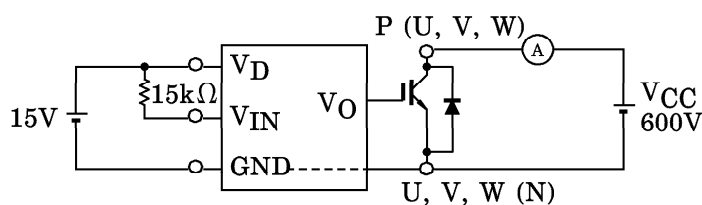
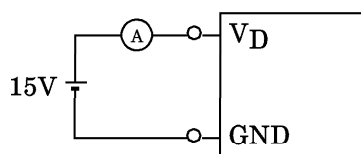
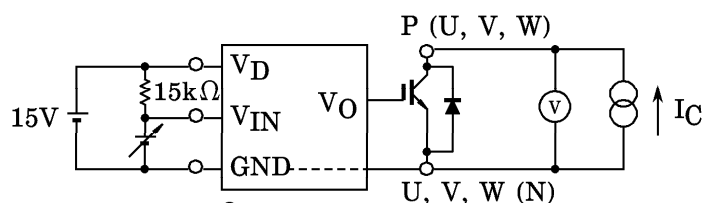
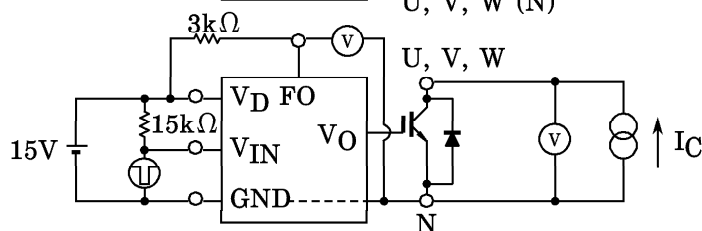
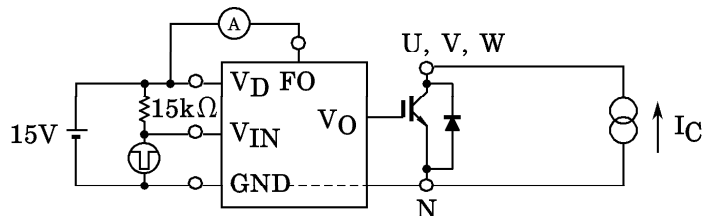
SYMBOL	ITEM	TEST CONDITION		SPEC			UNIT
				MIN.	TYP.	MAX.	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	V _D =15V I _{IN} =0mA	I _C =30A	—	2.1	2.7	V
			I _C =30A, T _j =125°C	—	—	3.0	
V _F	Forward Voltage	I _F =30A		—	2.0	2.7	V
t _{on}	Switching Time	V _{CC} =300V I _C =30A V _D =15V I _{IN} =1mA↔0mA Inductive Load		0.5	1.3	2.0	μs
t _c (on)				—	0.3	1.0	
t _{off}				0.5	1.0	2.0	
t _c (off)				—	0.5	1.5	
t _{rr}				—	0.15	0.25	
I _{CES}	Collector Cut-off Current	V _{CE} =600V	T _j =25°C	—	—	1	mA
			T _j =125°C	—	—	20	

Control Part (T_j = 25°C)

SYMBOL	ITEM	TEST CONDITION	SPEC			UNIT
			MIN.	TYP.	MAX.	
I _D	Circuit Current	V _D = 15V	High Side	6	12	18
			Low Side	11	23	35
V _{IN (on)}	Input On Signal Voltage	—		1.0	1.3	1.6
V _{IN (off)}	Input Off Signal Voltage			1.5	1.8	2.1
I _{FO}	Foul Output Current (Protection)	V _D = 15V, V _{FO} = 15V		3	5	7
	Foul Output Current (Normal)			—	—	1
OC	Over Current Protection Trip Level	V _D = 15V		46	55	—
		V _D = 15V, T _j ≤ 125°C		39	—	—
t _{off (OC)}	Over Current Cut Off Time	V _D = 15V		5	10	18
OT	Over Temperature Protection	Trip Level		100	110	120
		Reset Level		80	90	100
UV	Control Supply Under-Voltage Protection	Trip Level		11.3	12.0	12.7
UV _r		Reset Level		11.8	12.5	13.2
t _{FO}	Foul Output Pulse Width	V _D = 15V		5	10	15

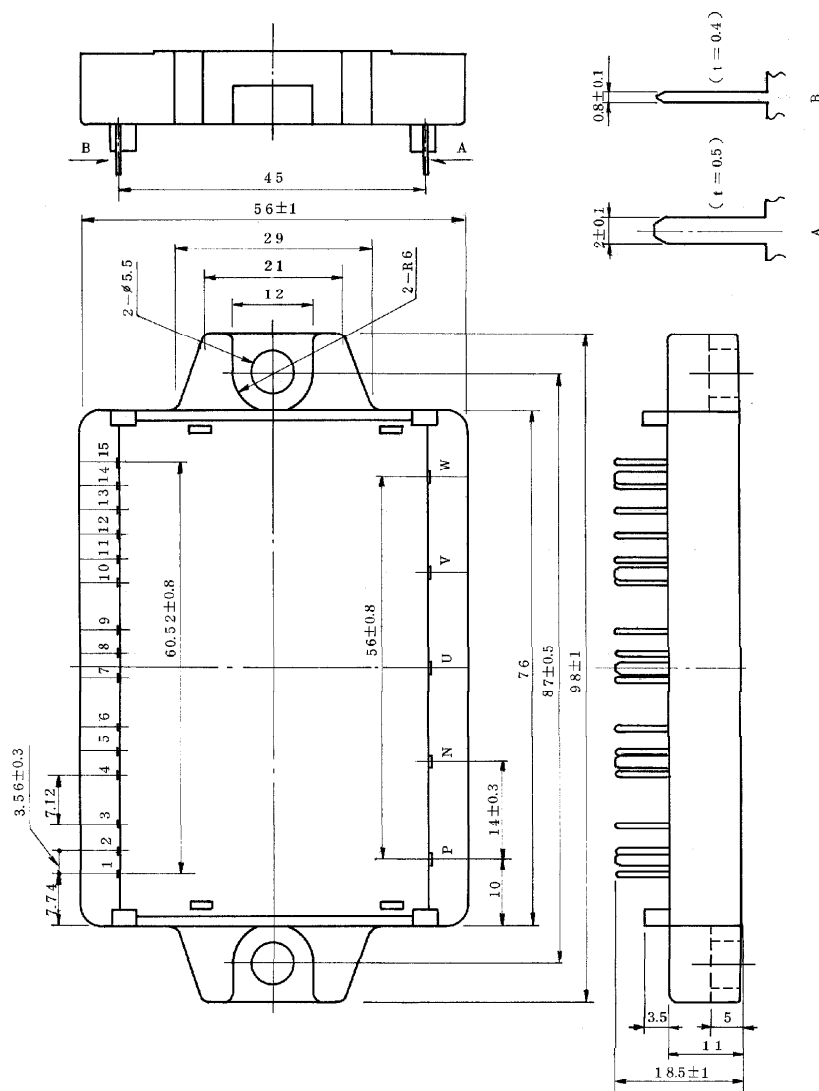
Thermal Resistance (T_j = 25°C)

SYMBOL	ITEM	TEST CONDITION	SPEC			UNIT
			MIN.	TYP.	MAX.	
R _{th (j-c)}	Junction to Case Thermal Resistance	INV. IGBT	—	—	1.25	°C/W
R _{th (j-c)}		INV. FWD	—	—	3.75	
R _{th (c-f)}	Case to Fin Thermal Resistance with compound	—	—	0.2	—	

ELECTRICAL CHARACTERISTICS TEST CIRCUIT ($V_{CE(sat)}$, V_F , I_{CES} , I_D , V_{IN} , I_{FO} , t_{FO})a) $V_{CE(sat)}$ b) V_F c) I_{CES} d) I_D e) $V_{IN(OFF)}$
 $V_{IN(ON)}$ f) t_{FO} g) I_{FO} 

OUTLINE : TOSHIBA 2-99E1A

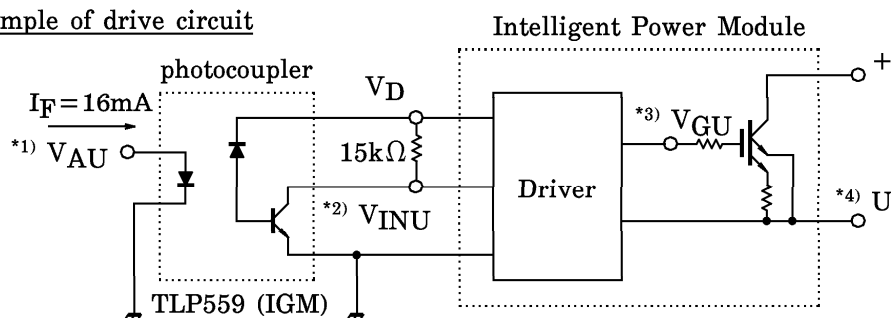
Unit in mm



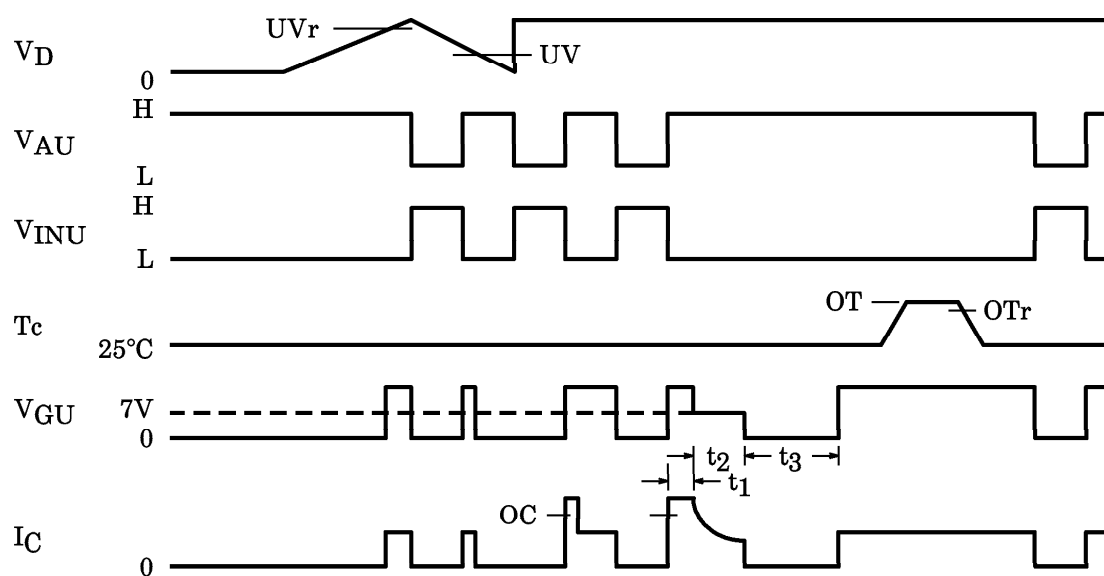
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TIMING CHART (High side)

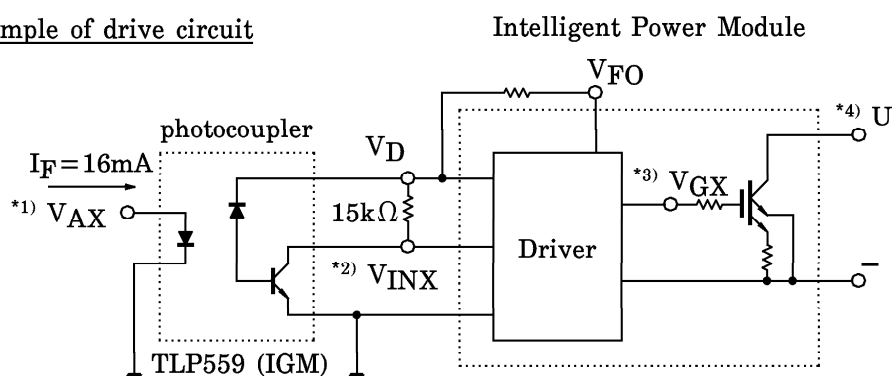
Typical example of drive circuit



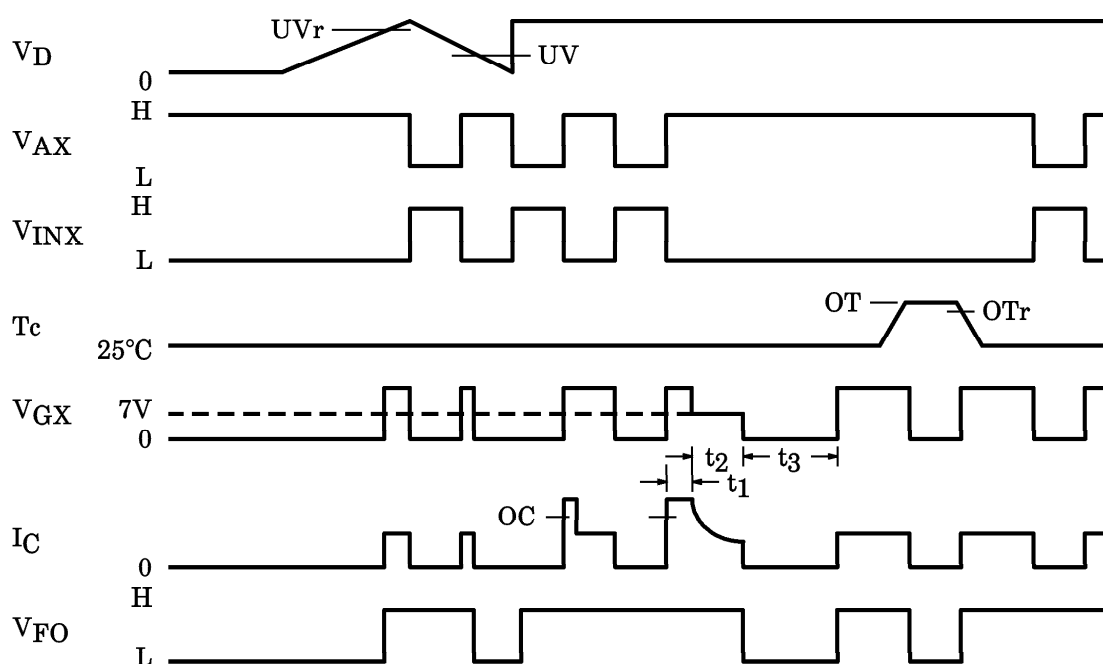
- *1) or V_{AV} , V_{AW}
 *2) or V_{INV} , V_{INW}
 *3) or V_{GV} , V_{GW}
 *4) or V , W



- UV : Under-Voltage Trip Level
 UVr : Under-Voltage Reset Level
 OT : Over Temperature Trip Level
 OTr : Over Temperature Reset Level
 OC : Over Current

TIMING CHART (Low side)
Typical example of drive circuit


- *1) or V_{AY} , V_{AZ}
 *2) or $V_{IN Y}$, $V_{IN Z}$
 *3) or V_{GY} , V_{GZ}
 *4) or V , W



UV : Under-Voltage Trip Level
 UVr : Under-Voltage Reset Level
 OT : Over Temperature Trip Level
 OTr : Over Temperature Reset Level
 OC : Over Current

t_1 : 2.5 μ s (Typ.)
 t_2 : 10 μ s (Typ.)
 t_3 : 10ms (Typ.)

